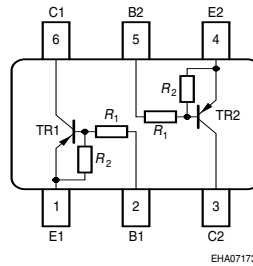
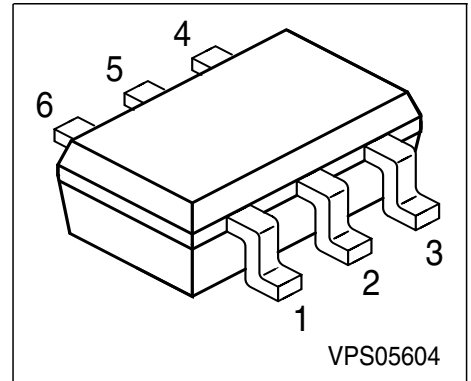


PNP Silicon Digital Transistor Array

- Switching circuit, inverter, interface circuit, driver circuit
- Two (galvanic) internal isolated Transistors with good matching in one package
- Built in bias resistor ($R_1=10k\Omega$, $R_2=47k\Omega$)



Type	Marking	Pin Configuration				Package		
BCR185S	WNs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Emitter-base voltage	V_{EBO}	6	
Input on Voltage	$V_{i(on)}$	20	
DC collector current	I_C	100	mA
Total power dissipation, $T_S = 115\text{ }^\circ\text{C}$	P_{tot}	250	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point ¹⁾	R_{thJS}	≤ 140	K/W
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¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

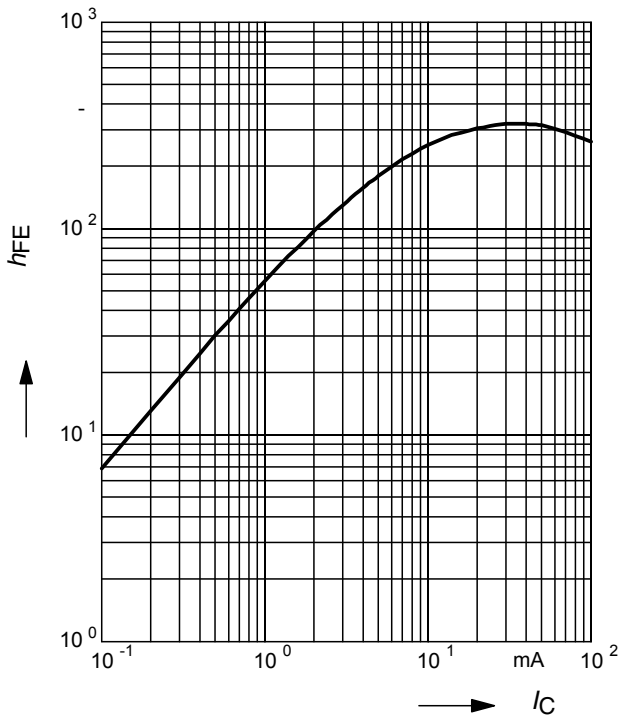
Electrical Characteristics at $T_A=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100\ \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10\ \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Emitter-base breakdown voltage $I_E = 10\ \mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	-	-	-	
Collector cutoff current $V_{CB} = 40\ \text{V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter cutoff current $V_{EB} = 6\ \text{V}, I_C = 0$	I_{EBO}	-	-	167	μA
DC current gain 1) $I_C = 5\ \text{mA}, V_{CE} = 5\ \text{V}$	h_{FE}	70	-	-	-
Collector-emitter saturation voltage1) $I_C = 10\ \text{mA}, I_B = 0.5\ \text{mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100\ \mu\text{A}, V_{CE} = 5\ \text{V}$	$V_{i(off)}$	0.5	-	1	
Input on Voltage $I_C = 2\ \text{mA}, V_{CE} = 0.3\ \text{V}$	$V_{i(on)}$	0.5	-	1.4	
Input resistor	R_1	7	10	13	$\text{k}\Omega$
Resistor ratio	R_1/R_2	0.19	0.21	0.24	-
AC Characteristics					
Transition frequency $I_C = 10\ \text{mA}, V_{CE} = 5\ \text{V}, f = 100\ \text{MHz}$	f_T	-	200	-	MHz
Collector-base capacitance $V_{CB} = 10\ \text{V}, f = 1\ \text{MHz}$	C_{cb}	-	3	-	pF

 1) Pulse test: $t < 300\ \mu\text{s}; D < 2\%$

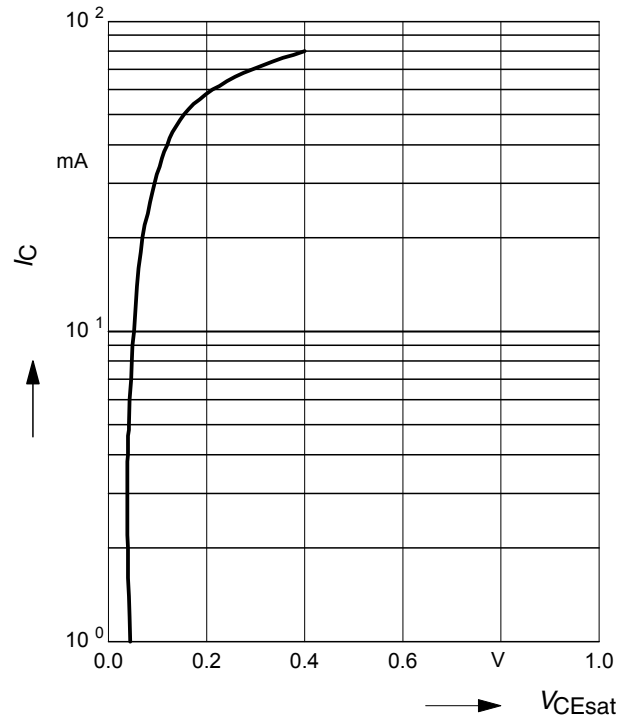
DC Current Gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



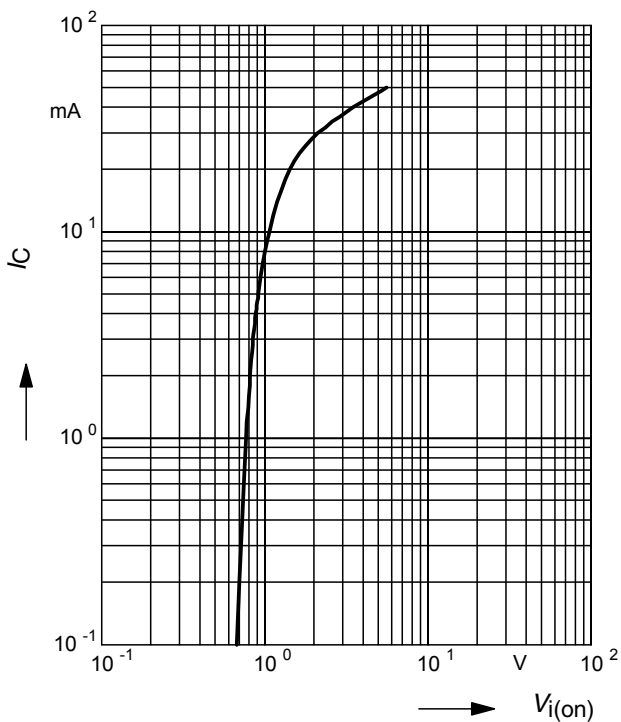
Collector-Emitter Saturation Voltage $V_{CEsat} = f(I_C), h_{FE} = 20$

$V_{CEsat} = f(I_C), h_{FE} = 20$



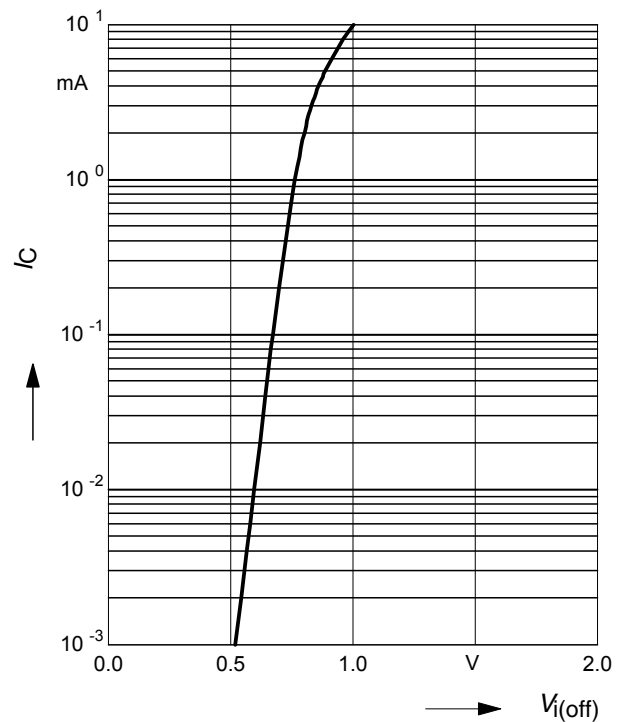
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$ (common emitter configuration)

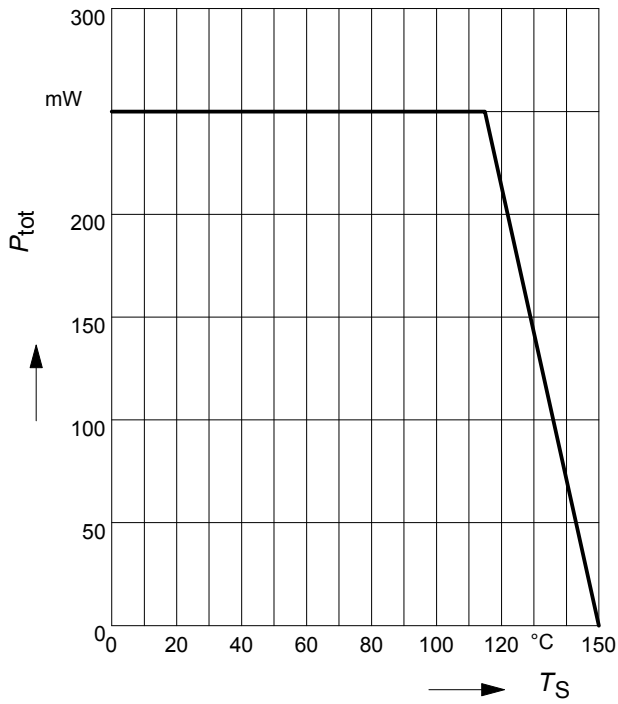


Input off voltage $V_{i(off)} = f(I_C)$

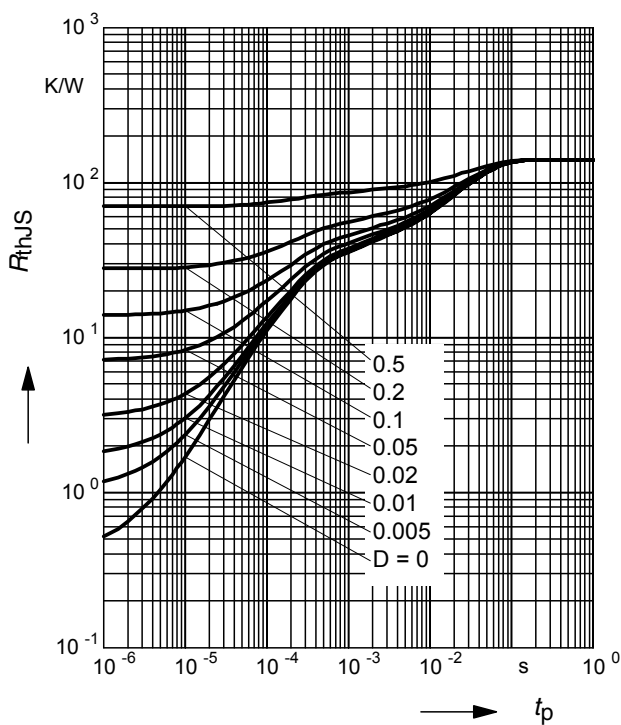
$V_{CE} = 5V$ (common emitter configuration)



Total power dissipation $P_{tot} = f(T_S)$



Permissible Pulse Load $R_{thJS} = f(t_p)$



Permissible Pulse Load

$P_{totmax} / P_{totDC} = f(t_p)$

